

Amendments to the Specification:

Please replace paragraph 21 with the following amended paragraph:

[21] The present mask structure also includes first anti-static guard ring structure 403, which surrounds the periphery of the active region, on the mask structure. The first anti-static guard ring structure serves as isolation between the active region and the second anti-static guard ring structure. The first guard ring structure can be a trench region, which is filled with a dielectric layer. The trench region is free from an overlying metal layer for patterning. Referring to Figure 5, guard ring 403 is formed in the mask structure, which also includes pattern regions 505, 507 501. The trench region is often 20 micron and less in width and also 300 nm to about 1000 nm in thickness, depending upon the embodiment.